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MEASUREMENTS I

Chairman: R. D. Pollard—University of Leeds, UK

Session Abstract: Recent years have seen major challenges in the characterisation of active devices which were the result of advances in microwave semiconductor technology. In addition to a range of new devices, higher frequencies and a variety of transmission media, the advent of the monolithic microwave integrated circuit and the prospect of mass production has added new impetus. There has been a significant increase in activity in measurements which can provide useful large signal information for use in the design and modelling processes. On-wafer probing techniques are now accepted on an industry-wide basis. The techniques require development to provide increased accuracy and extended frequency capabilities.

The session begins by focussing on large signal techniques applied to improving the design of circuits employing microwave FETs. Small signal s-parameter measurements are applied to better the understanding of both FETs and the newer HEMTs. Two papers on contrasting probing techniques demonstrate the scope for remaining development.

2:00 pm–3:30 pm, May 25, 1988
Jacob Javits Convention Center, Hall 1E
Room 4